

NPN RF POWER TRANSISTOR

DESCRIPTION:

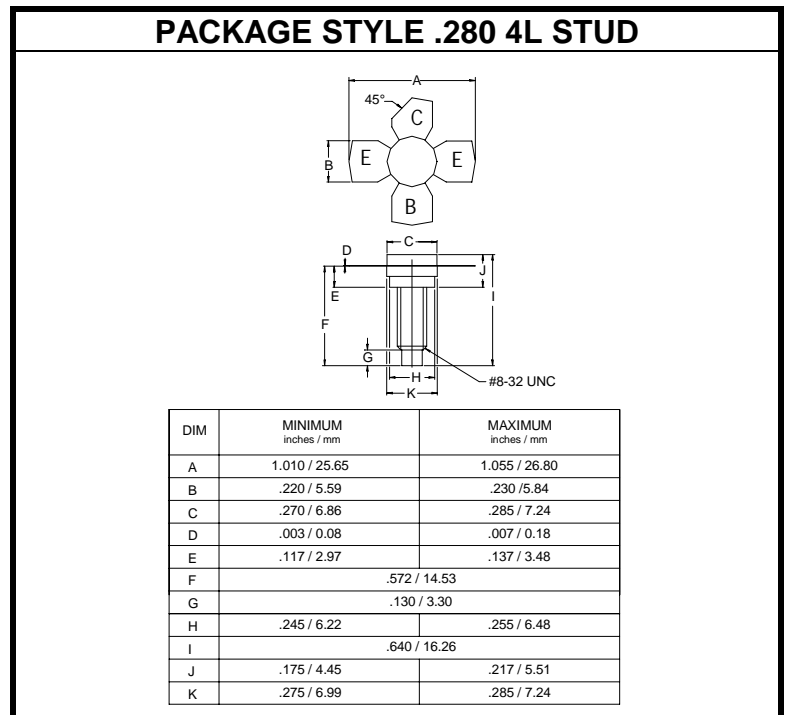
The **MRF5174** is a Common Emitter Device Designed for Class A, AB and C Amplifier Applications in the 225 to 400 MHz Band.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	0.5 A
V_{CB0}	40 V
P_{DISS}	8.75 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
θ_{JC}	20 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 1.0 mA	40			V
BV_{CEO}	I _C = 1.0 mA	28			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CB0}	V _{CB} = 28 V			500	μA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		120	---
C_{OB}	V _{CB} = 28 V f = 1.0 MHz			5.0	pF
P_G	V _{CE} = 28 V P _{OUT} = 2.0 W f = 400 MHz	12	13		dB
η_C		50			%